BLA1011-200R; BLA1011S-200R

Avionics LDMOS transistors

Rev. 01 — 23 February 2010 Product data sheet

1. Product profile

1.1 General description

200 W LDMOS avionics power transistor for transmitter applications at frequencies from 1030 MHz to 1090 MHz.

Table 1. Typical performance

RF performance at T_h = 25 °C in a common source class-AB test circuit; I_{Dq} = 150 mA; typical values.

Mode of operation	Conditions	V_{DS} (V)	P_L (W)	G_p (dB)	η_D (%)	t_r (ns)	t_f (ns)
Pulsed class-AB: 1030 MHz to 1090 MHz	t_p = 50 µs; δ = 2 %	36	200	15	50	35	6
	t_p = 128 µs; δ = 2 %	36	250	14	50	35	6
	t_p = 340 µs; δ = 1 %	36	250	14	50	35	6

CAUTION

This device is sensitive to ElectroStatic Discharge (ESD). Therefore care should be taken during transport and handling.

1.2 Features and benefits

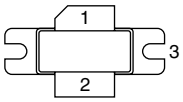
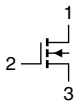
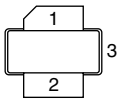
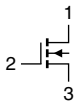
- Typical pulsed class-AB performance at a frequencies from 1030 MHz to 1090 MHz, a supply voltage of 36 V and an I_{Dq} of 150 mA:
  - Load power ≥ 200 W
  - Gain ≥ 13 dB
  - Efficiency ≥ 45 %
  - Rise time ≤ 50 ns
  - Fall time ≤ 50 ns
- High power gain
- Easy power control
- Excellent ruggedness
- Source on mounting flange eliminates DC isolators, reducing common mode inductance
- Compliant to Directive 2002/95/EC, regarding Restriction of Hazardous Substances (RoHS)

1.3 Applications

- Avionics transmitter applications in the 1030 MHz to 1090 MHz frequency range.

2. Pinning information

Table 2. Pinning

Pin	Description		Simplified outline	Graphic symbol
BLA1011-200R (SOT502A)				
1	drain			
2	gate			
3	source	[1]		
				sym039
BLA1011S-200R (SOT502B)				
1	drain			
2	gate			
3	source	[1]		
				sym039

[1] Connected to flange.

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BLA1011-200R	-	flanged LDMOST ceramic package; 2 mounting holes; 2 leads	SOT502A
BLA1011S-200R	-	earless flanged LDMOST ceramic package; 2 leads	SOT502B

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage		-	75	V
V_{GS}	gate-source voltage		-	±22	V
P_{tot}	total power dissipation	$T_h \leq 25$ °C; $t_p = 50$ µs; $\delta = 2$ %	-	700	W
T_{stg}	storage temperature		–65	+150	°C
T_j	junction temperature		-	200	°C

5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions		Typ	Unit
$Z_{th(j-h)}$	transient thermal impedance from junction to heatsink	T_h = 25 °C	[1]	0.15	K/W

[1] Thermal resistance is determined under RF operating conditions; t_p = 50 µs, δ = 10 %.

6. Characteristics

Table 6. Characteristics

T_j = 25 °C unless otherwise specified

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{(BR)DSS}$	drain-source breakdown voltage	V_{GS} = 0 V; I_D = 3 mA	75	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	V_{DS} = 10 V; I_D = 300 mA	4	-	5	V
I_{DSS}	drain leakage current	V_{GS} = 0 V; V_{DS} = 36 V	-	-	1	µA
I_{DSX}	drain cut-off current	V_{GS} = $V_{GS(th)}$ + 9 V; V_{DS} = 10 V	45	-	-	A
I_{GSS}	gate leakage current	V_{GS} = ±20 V; V_{DS} = 0 V	-	-	1	µA
g_{fs}	forward transconductance	V_{DS} = 10 V; I_D = 10 A	-	9	-	S
$R_{DS(on)}$	drain-source on-state resistance	V_{GS} = 9 V; I_D = 10 A	-	60	-	mΩ

7. Application information

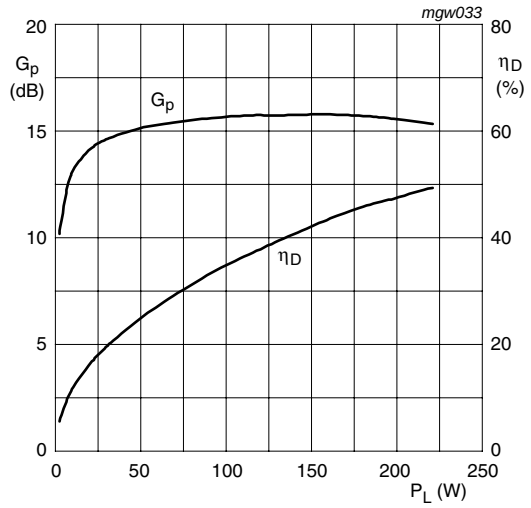
Table 7. Application information

RF performance in a common source pulsed class-AB circuit; (t_p = 50 µs; δ = 2 %); f = 1030 MHz and 1090 MHz; T_h = 25 °C; $Z_{th(mb-h)}$ = 0.15 K/W; I_{Dq} = 150 mA; unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{DS}	drain-source voltage		-	36	-	V
P_L	output power	t_p = 50 µs; δ = 2 %	-	200		W
G_p	power gain	P_L = 200 W	13	-		dB
η_D	drain efficiency	t_p = 50 µs; δ = 2 %	45	-		%
t_r	rise time		-	-	50	ns
t_f	fall time		-	-	50	ns

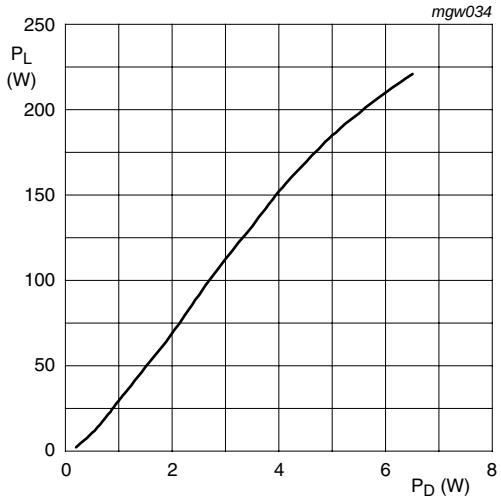
7.1 Ruggedness in class-AB operation

The BLA1011-200R and BLA1011S-200R are capable of withstanding a load mismatch corresponding to VSWR = 5 : 1 through all phases under the following conditions: V_{DS} = 36 V; f = 1030 MHz to 1090 MHz at rated load power.



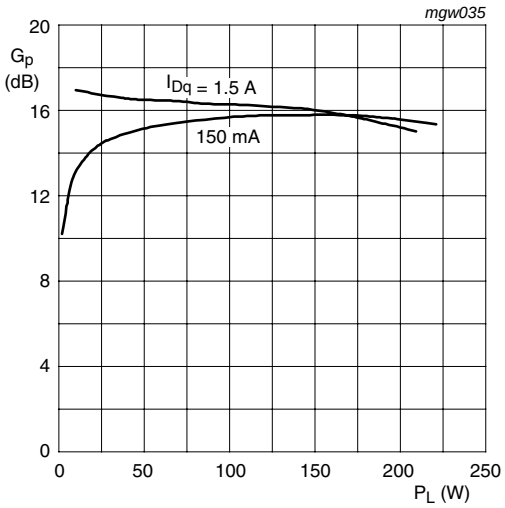
V_{DS} = 36 V; I_{Dq} = 150 mA; f = 1060 MHz; t_p = 50 µs; δ = 2 %

Fig 1. Power gain and drain efficiency as functions of load power; typical values



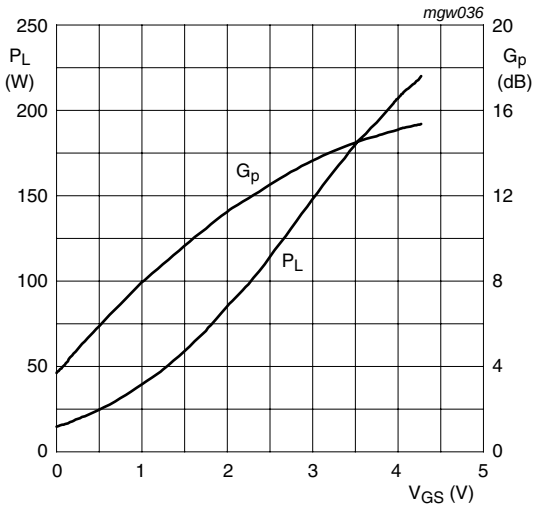
V_{DS} = 36 V; I_{Dq} = 150 mA; f = 1060 MHz; t_p = 50 µs; δ = 2 %

Fig 2. Load power as a function of drive power; typical values



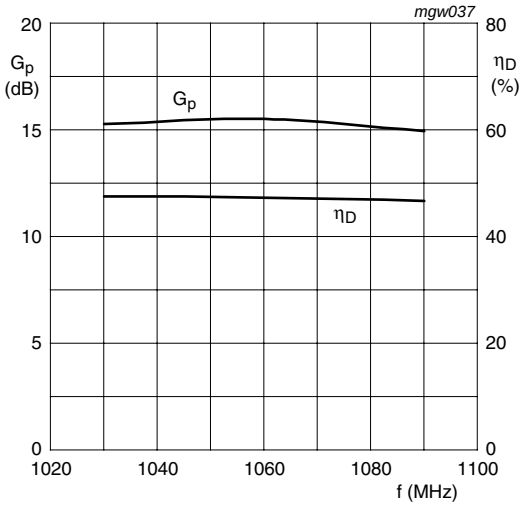
V_{DS} = 36 V; f = 1060 MHz; t_p = 50 µs; δ = 2 %

Fig 3. Power gain as a function of load power; typical values



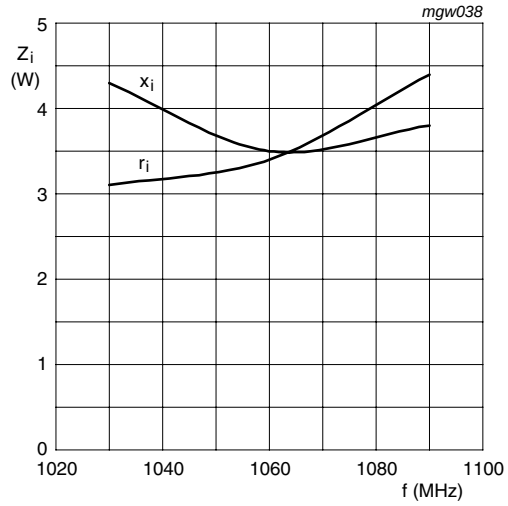
V_{DS} = 36 V; I_{Dq} = 150 mA; P_i = 5.5 W; f = 1060 MHz; t_p = 50 µs; δ = 2 %

Fig 4. Load power and power gain as functions of gate-source voltage; typical values



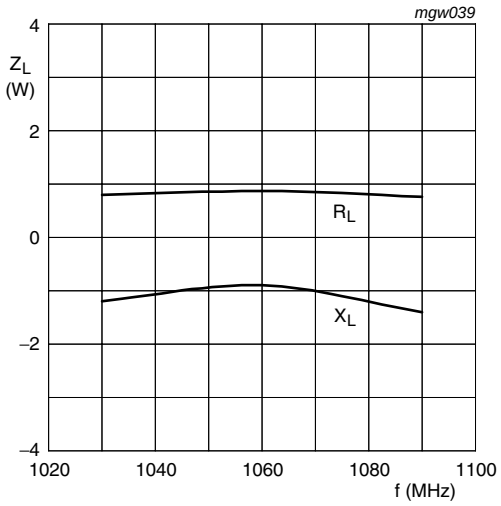
V_{DS} = 36 V; I_{Dq} = 150 mA; P_L = 200 W; t_p = 50 µs; δ = 2 %

Fig 5. Power gain and drain efficiency a functions of frequency; typical values



V_{DS} = 36 V; I_{Dq} = 150 mA; P_L = 200 W; t_p = 50 µs; δ = 2 %

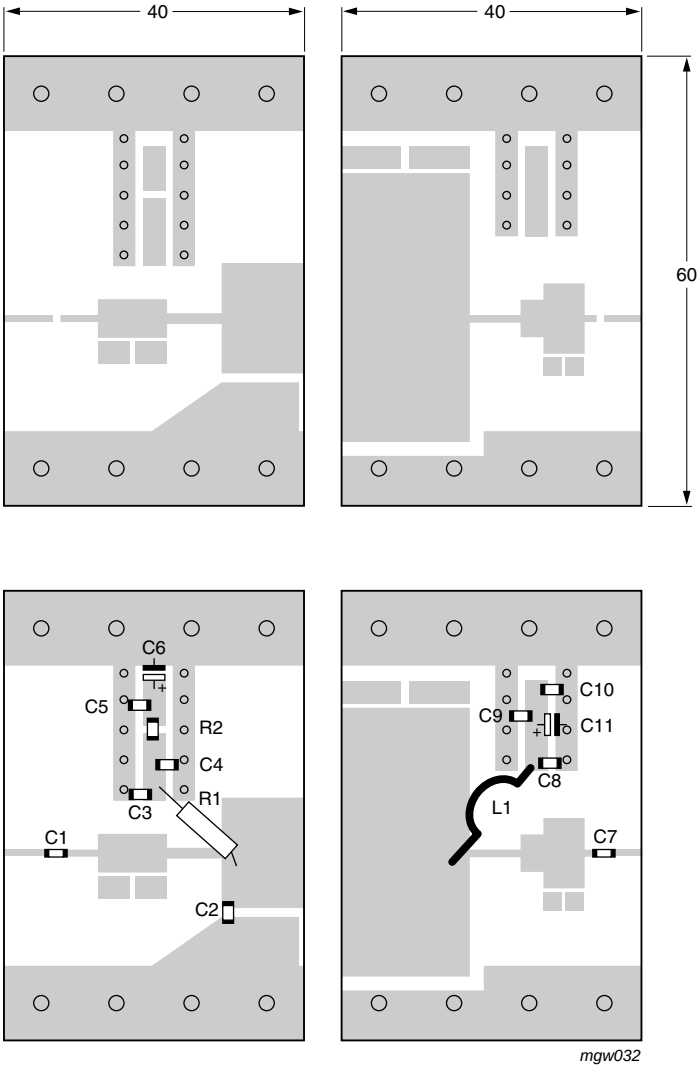
Fig 6. Input Impedance as a function of frequency (series components); typical values



V_{DS} = 36 V; I_{Dq} = 150 mA; P_L = 200 W; t_p = 50 µs; δ = 2 %

Fig 7. Load impedance as a function of frequency (series components); typical values

8. Test information



Dimensions in mm.

The components are situated on one side of the copper-clad Duroid Printed-Circuit Board (PCB) with ε_r = 6.2 and thickness 0.64 mm.

The other side is unetched and serves as a ground plane.

See Table 8 for list of components.

Fig 8. Component layout for 1030 MHz to 1090 MHz test circuit

Table 8. List of components (see Figure 8)

Component	Description	Value	Dimensions
C1	multilayer ceramic chip capacitor [1]	39 pF	
C2	multilayer ceramic chip capacitor [2]	4.3 pF	
C3	multilayer ceramic chip capacitor [1]	11 pF	
C4, C7	multilayer ceramic chip capacitor [1]	62 pF	
C5	multilayer ceramic chip capacitor [1]	100 pF	
C6	electrolytic capacitor	47 µF; 20 V	
C8	multilayer ceramic chip capacitor [2]	20 pF	
C9	multilayer ceramic chip capacitor [1]	47 pF	
C10	multilayer ceramic chip capacitor [3]	1.2 nF	
C11	electrolytic capacitor	47 µF; 63 V	
L1	Ω-shaped enamelled 1 mm copper wire		length = 38 mm
R1	metal film resistor	301 Ω	
R2	SMD 0508 resistor	18 Ω	

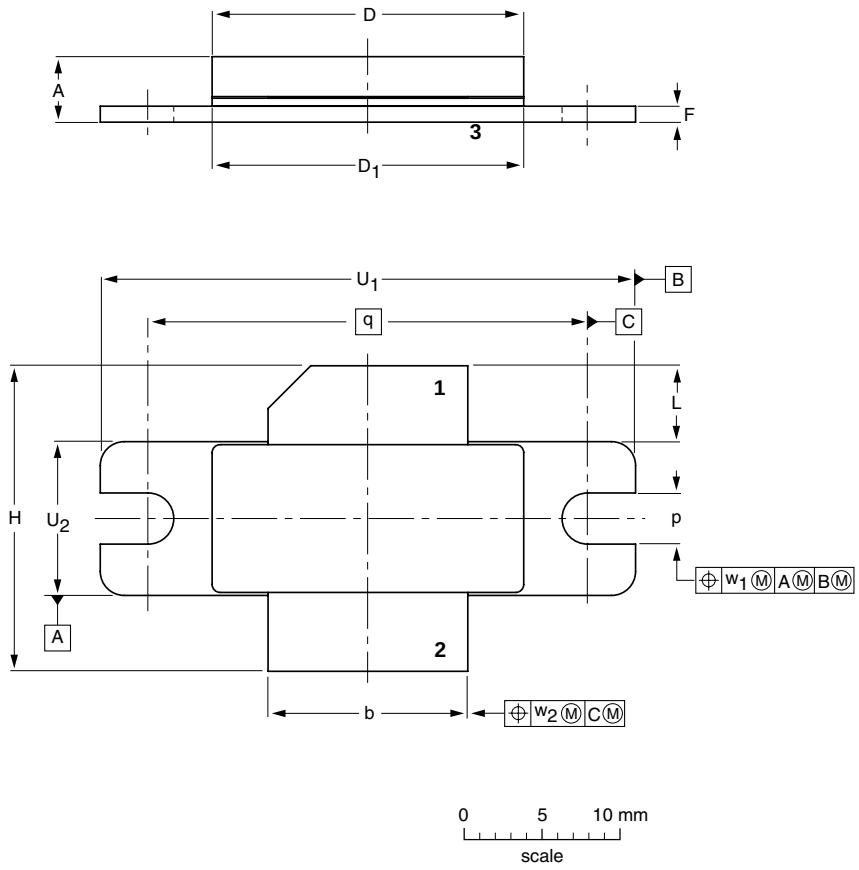
[1] American Technical Ceramics type 100A or capacitor of same quality.

[2] American Technical Ceramics type 100B or capacitor of same quality.

[3] American Technical Ceramics type 700 or capacitor of same quality.

9. Package outline

Flanged LDMOST ceramic package; 2 mounting holes; 2 leads **SOT502A**



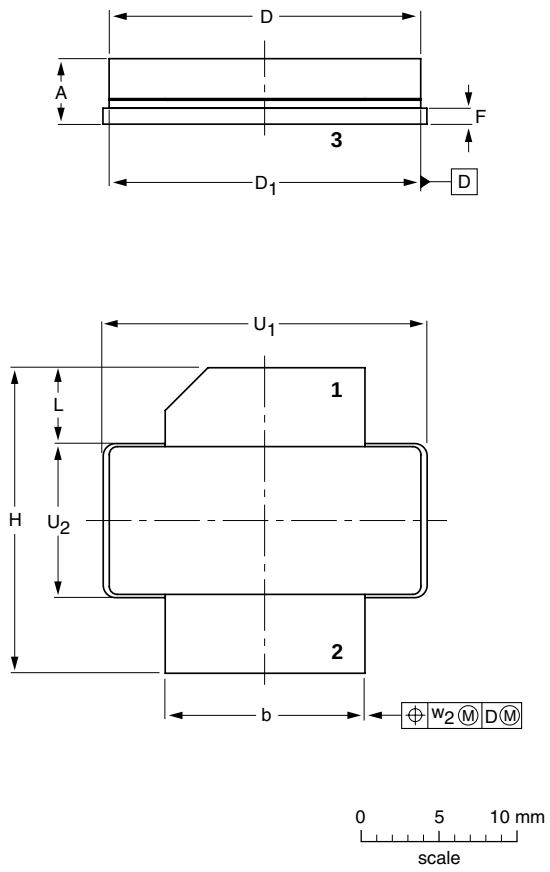
DIMENSIONS (millimetre dimensions are derived from the original inch dimensions)

UNIT	A	b	c	D	D_1	E	E_1	F	H	L	p	Q	q	U_1	U_2	w_1	w_2
mm	4.72 3.43	12.83 12.57	0.15 0.08	20.02 19.61	19.96 19.66	9.50 9.30	9.53 9.25	1.14 0.89	19.94 18.92	5.33 4.32	3.38 3.12	1.70 1.45	27.94	34.16 33.91	9.91 9.65	0.25	0.51
inches	0.186 0.135	0.505 0.495	0.006 0.003	0.788 0.772	0.786 0.774	0.374 0.366	0.375 0.364	0.045 0.035	0.785 0.745	0.210 0.170	0.133 0.123	0.067 0.057	1.100	1.345 1.335	0.390 0.380	0.01	0.02

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT502A						~~99-12-28~~ 03-01-10

Fig 9. Package outline SOT502A

Earless flanged LDMOST ceramic package; 2 leads **SOT502B**



DIMENSIONS (millimetre dimensions are derived from the original inch dimensions)

UNIT	A	b	c	D	D_1	E	E_1	F	H	L	Q	U_1	U_2	w_2
mm	4.72 3.43	12.83 12.57	0.15 0.08	20.02 19.61	19.96 19.66	9.50 9.30	9.53 9.25	1.14 0.89	19.94 18.92	5.33 4.32	1.70 1.45	20.70 20.45	9.91 9.65	0.25
inches	0.186 0.135	0.505 0.495	0.006 0.003	0.788 0.772	0.786 0.774	0.374 0.366	0.375 0.364	0.045 0.035	0.785 0.745	0.210 0.170	0.067 0.057	0.815 0.805	0.390 0.380	0.010

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT502B						~~03-01-10~~ 07-05-09

Fig 10. Package outline SOT502B

10. Abbreviations

Table 9. Abbreviations

Acronym	Description
I_{Dq}	quiescent drain current
LDMOS	Laterally Diffused Metal-Oxide Semiconductor
LDMOST	Laterally Diffused Metal-Oxide Semiconductor Transistor
RF	Radio Frequency
SMD	Surface Mount Device
VSWR	Voltage Standing-Wave Ratio

11. Revision history

Table 10. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BLA1011-200R_1011S-200R_1	20100223	Product data sheet	-	-

12. Legal information

12.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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14. Contents

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